

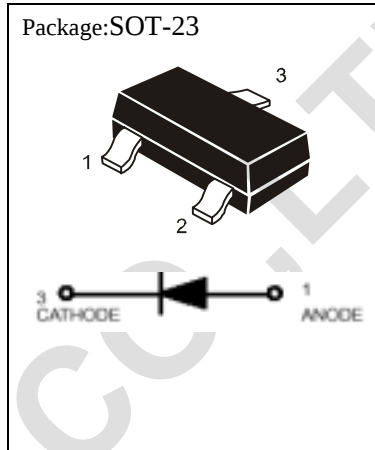
SURFACE MOUNT SWITCHING DIODE

- Low Leakage Current Applications
- Medium Speed Switching Times

ABSOLUTE MAXIMUM RATINGS at Ta=25°C

Characteristic	Symbol	Rating	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
Peak Forward Current	I_F	200	mAdc
Forward Continuous Current(Note)	I_{FM}	300	mAdc
Power Dissipation (Note)	P_D	300	mW
Derate Above 25°C		2.4	mW/°C
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-50-150	°C

Note:Diode Ceramic Substrate 10mm × 8.0mm × 0.7mm



ELECTRICAL CHARACTERISTICS at Ta=25°C

Characteristic	Symbol	Min	Max	Unit	Test Conditions
Forward Voltage	V_F		0.9	V	$I_F=1.0mA$
			1.0	V	$I_F=10mA$
			1.1	V	$I_F=50mA$
			1.25	V	$I_F=150mA$
Reverse Breakdown Voltage	$V_{(BR)}$	75	—	Vdc	$I_{BR} = 100 \mu A$
Reverse Voltage Leakage Current	I_R		5.0	μA	$V_R=75V$
			80	nA	$V_R=75V T_j=150^\circ C$
Capacitance	C_j		2.0	PF	$V_R=0 f=1.0MHz$
Reverse Recovery Time	T_{rr}		3.0	μs	$I_F=10mA$ to $I_R=10mA$

Note:Diode On Ceramic Substrate 10mm × 8.0mm × 0.7mm

DEVICE MARKING:

BAS116LT1=JV